

InGaAs QUADRANT PHOTODIODE



Description

2.525mm diameter Low Dark Current SiC Quadrant Photodiode with P on N construction and 22um gaps. Packaged in a TO-5 with a hermetic ultra flat fused quartz window cap.

Features

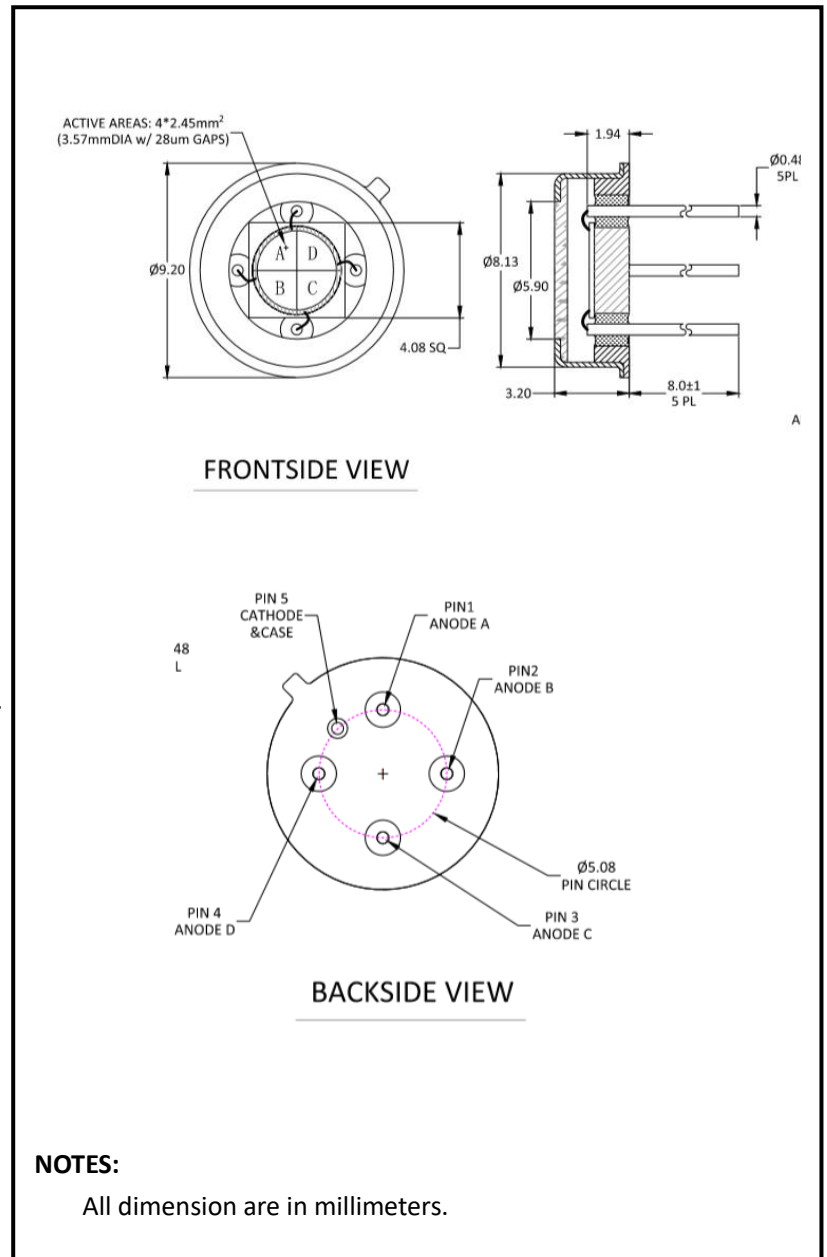
- *SiC quadrant photodiode
- *High responsivity and uniformity
- *Low noise and cross-talk between channels

General Ratings

- * High linearity
- * High reliability

Applications

- * UV Laser beam position sensor
- * Minuteness process controller
- * Optical tweezers
- * Laser guidance



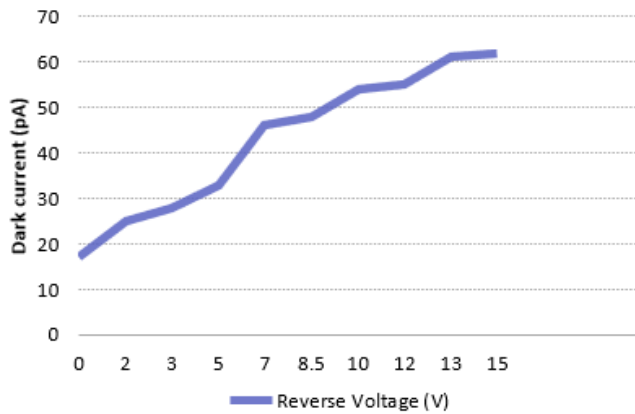
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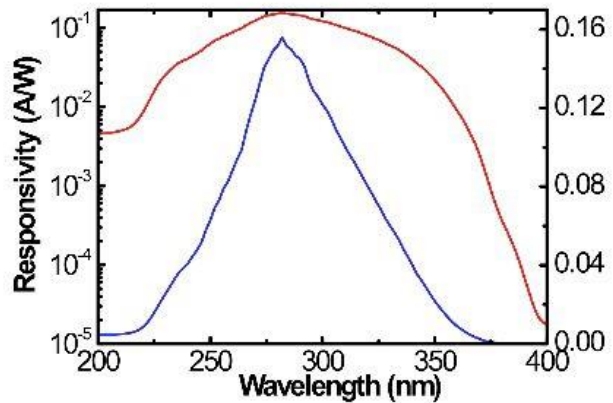
Absolute Maximum Ratings (Ta=25°C)

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Chip size	Dia.			Φ2.525		mm
Gap	d	element to element		22		um
Dark current	I _D	V _R =0V, Per channel		0.017		nA
		V _R =2.5V, Per channel		0.028		nA
Rise time	t _R	f=1MHz; λ=280nm; VR=5V, R _L =50Ω		10	30	ns
Junction Capacitance	C _J	V _R =0V f=1MHz		110		pF
		V _R =5V f=1MHz		109		pF
Crosstalk Channel- to -Channel		280nm, Adjacent Channels, VR=0V			3	%
Photo sensitivity	S _R	280nm		0.15		A/W
Spectral Application Range	λ _{range}		215		360	nm

■ Dark current vs. reverse voltage



■ Spectral response



■ Relative Junction Capacitance

VS. Voltage

